



Docket No. 740819-537

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)
Takeshi YAMASHITA et al.) Group Art Unit: 1765
Serial No. 09 826,098) Examiner: Kin Chan CHEN
Filed: April 5, 2001)
For: DRY ETCHING METHOD,) Date: April 18, 2003
FABRICATION METHOD FOR
SEMICONDUCTOR DEVICE, AND
DRY ETCHING APPARATUS

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TC 1700

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed December 18, 2002, please consider the following amendments and remarks in connection with the above-identified application.

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 10, fourth paragraph, please replace with:

--Next, as shown in FIG. 15C, the ions 88 in the plasma 87 are drawn into the silicon substrate 80 with application of the bias power. However, since the silicon oxide film 90 has been formed on the silicon substrate 80 as an object to be etched and an etching speed for the silicon oxide film is about one hundredth of an etching speed for silicon, etching performed with respect to the silicon substrate 80 hardly proceeds.--

14-11-2003 10:00:00

10-11-2003 10:00:00

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